

Amendments to the Drawings:

None

REMARKS/ARGUMENTS

Claims 11 and 19 have been amended to include the limitation of forming contact regions of the same conductivity type as the well regions. The Hsu patent teaches in col. 4, lines 41-46 that the source and drain regions 60, 62 are of opposite conductivity type to the well region 63. The well region 63 is p-type and the source and drain regions 60, 62 are n-type. Amended claims 11 and 19 are therefore allowable over the Hsu patent. Furthermore, claims 12-14 and 20-22 depend on claims 11 and 19 respectively and therefore contain all the limitations of these claims. Claims 12-14 and 20-22 are therefore also allowable over the cited art.

Referring to Figures 2(a) and 2(b) of the instant disclosure, the examiner is directed to claim 11 which comprises the limitations of forming at least a first 60 and second 65 active regions in said well region 20 by forming a contact isolation structure 32 in said well region between said first isolation region and said second isolation region, forming a gate dielectric layer 40 on said first active region and said second active region, and forming a gate layer 50 on said gate dielectric layer wherein said gate layer overlies said first active region 60, said second active region 65, and said contact isolation region 32. All the limitations to which the examiner refers in the response dated 12/10/2004 are clearly described in claim 11.

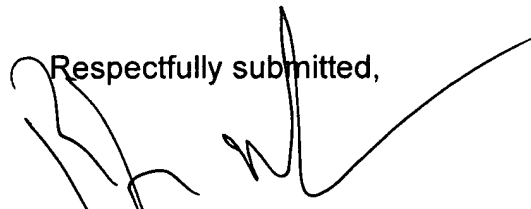
The examiner is now directed to the Hsu patent where, in Figure 2, first and second active regions are formed by forming the isolation structure 34. The subsequent gate structure 46 in the Hsu patent extends only over one of the active regions formed in Figure 2. From Figure 7 of the Hsu patent, this would be the active region formed to the left of the isolation structure 34. Claim 11 requires the gate layer (46 in the Hsu patent) to overlie said first active region, said second active region, and said contact isolation region. This is not shown in the Hsu patent and claim 11 is allowable over the Hsu patent under 102(b). Furthermore, claims 12-14 depend on claim 11 and therefore contain all the limitations of claim 11. The Lin patent does not contain the feature described above and claims 12-14 are therefore also allowable over the Hsu patent either singly or in combination with the Lin patent.

In light of the above, it is respectfully submitted that the present application is in condition for allowance, and notice to that effect is respectfully requested.

While it is believed that the instant response places the application in condition for allowance, should the Examiner have any further comments or suggestions, it is respectfully requested that the Examiner contact the undersigned in order to expeditiously resolve any outstanding issues.

To the extent necessary, Applicants petition for an Extension of Time under 37 CFR 1.136. Please charge any fees in connection with the filing of this paper, including extension of time fees, to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.

Respectfully submitted,



Peter K. McLarty
Attorney for Applicants
Reg. No. 44,923

Texas Instruments Incorporated
P.O. Box 655474, MS 3999
Dallas, TX 75265
(972) 917-4258